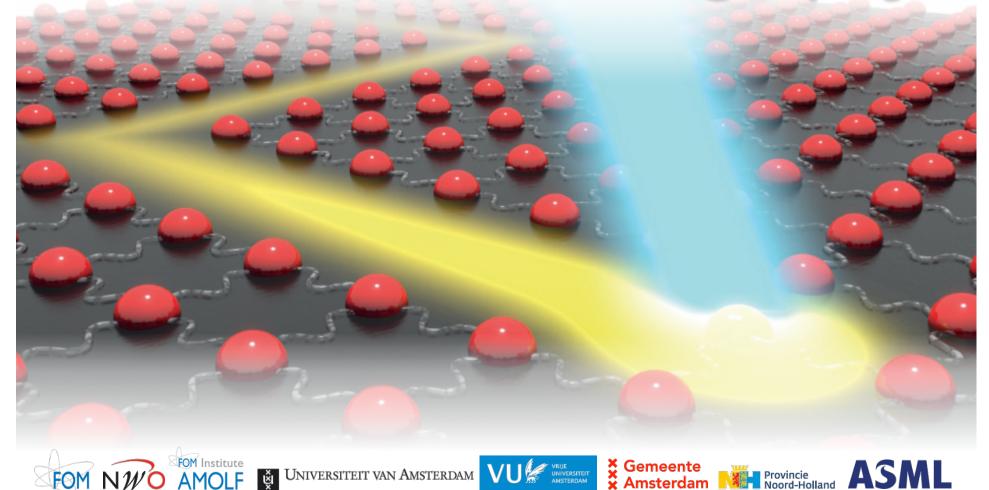


The Advanced Research Center for Nanolithography





The Advanced Research Center for Nanolithography

MISSION

The research of ARCNL focuses on the fundamental physics that is involved in or related to current and future technologies that are or will be employed in the context of lithography and nanolithography, primarily for the semiconductor industry.

PARTNERS

Foundation for Fundamental Research on Matter (FOM/NWO), University of Amsterdam, VU University Amsterdam, ASML

LOCATION

Amsterdam Science Park











ARC: birth of a new concept



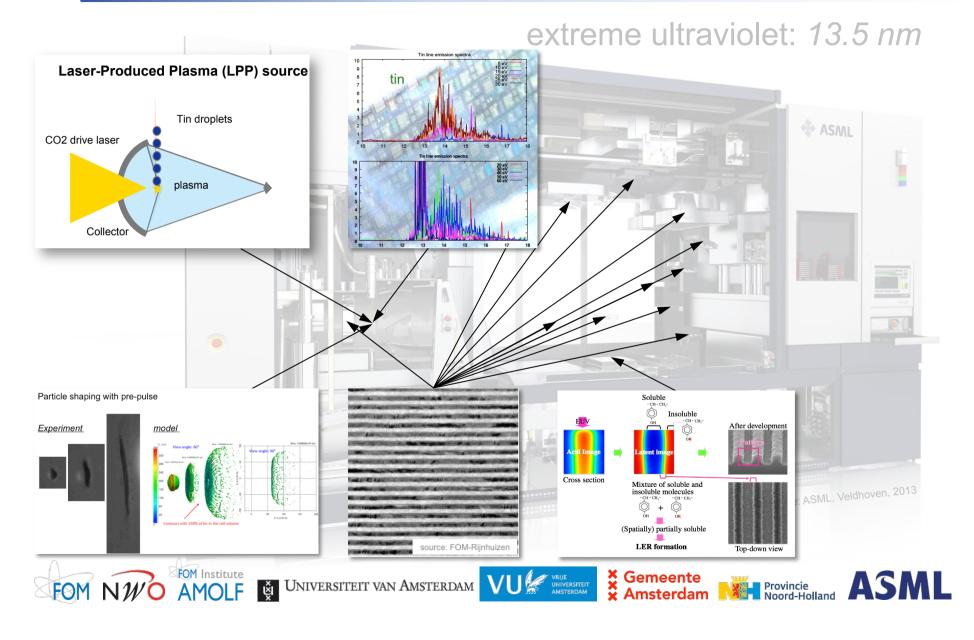


EUV lithography



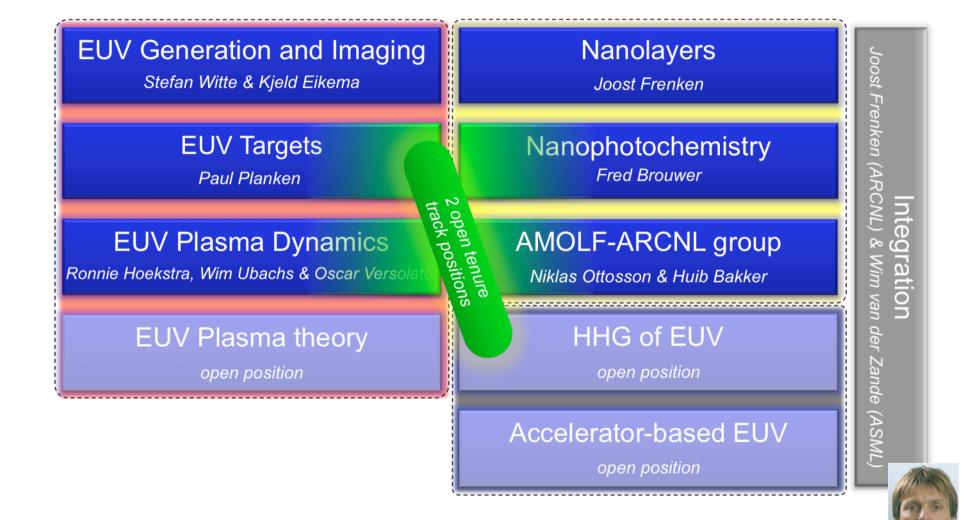


EUV lithography











Temporary labs and offices



 Temporary offices (capacity 96 people)
In use since end of December 2014 Temporary laboratory 400 m² lab space In use since mid October 2014



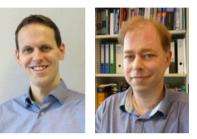
Long-term housing (Matrix-VII) in preparation (complete in 2018)

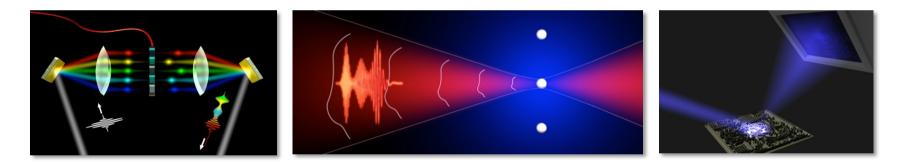




EUV Generation and Imaging

Stefan Witte & Kjeld Eikema





- Adaptive wavefront control IR pulse: spatial shape (plasma production) & temporal shape (EUV emission from dynamic plasma)
- High-harmonic generation (HHG) source(s) of EUV
- Contribute to Plasma Dynamics Group (IR pump EUV probe spectroscopy)
- Coherent EUV-based lenseless imaging (e.g. metrology)

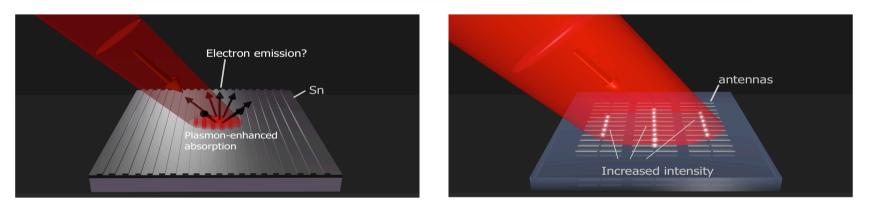




EUV Targets







- IR on nanostructured Sn surfaces: in-coupling e.g. via surface plasmon + "lattice"
- Nano-antenna structures
- Time-resolved measurements
- Fluid dynamics: interplay of IR pulse droplet shape plasma formation (link with work by Hanneke Gelderblom c.s.: part of FOM-IPP Detlef Lohse (UT) – ASML)



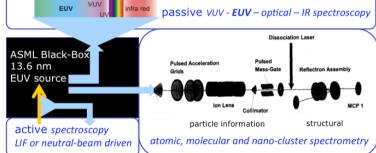


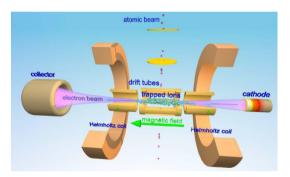
EUV Plasma Dynamics

Ronnie Hoekstra, Wim Ubachs & Oscar Versolato









- Analysis of species, abundancies, energies in plasma using optical spectroscopy and mass spectroscopy highly charged ions, radicals, molecules, clusters
- Support data (cross sections, reference spectra) on highly charged ions + highly excited (hollow) atoms + interaction with surfaces (ZERNIKELEIF and CRYRING)
- Electron Beam Ion Trap

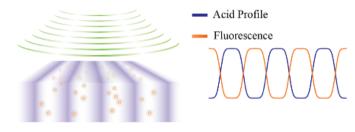


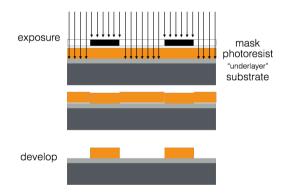


Nanophotochemistry

Fred Brouwer







- EUV interference lithography (SLS, ARCNL)
- Look inside photoresist: fluorescent probes
- New resist concepts: molecular glasses, cleavable polymers, polymer brushes, inorganic materials
- EUV absorption in 'underlayer'



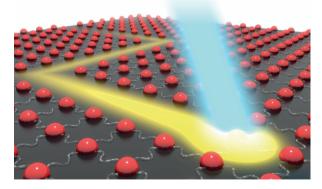


AMOLF-ARCNL group

Niklas Ottosson & Huib Bakker



- EUV Photoelectron specroscopy e.g. EUV-exposed surfaces, photoresist
- Further ARCNL-AMOLF projects





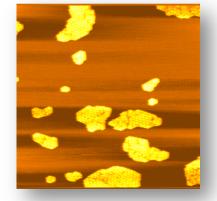


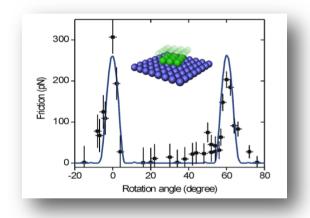
Nanolayers











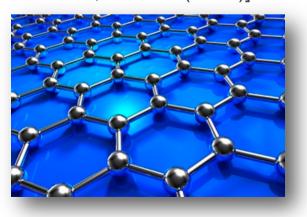
- Live STM: atomic-scale formation of interfaces (multilayer mirrors for 13.5 and 6.5 nm) link with FOM-Focus Group Fred Bijkerk (UT)
- Live STM: atomic-scale formation of graphene and look-alikes (e.g. coatings)
- Friction: atomic-scale origin and novel 'tricks': superlubricity, thermolubricity (handle on friction and contact forces)

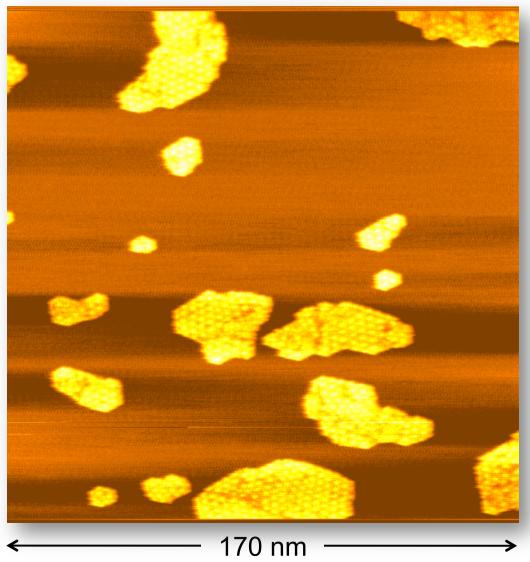
ARCNL **ARCNL ARCNL ARCNL**

Growth of graphene (and look-alikes)

Rh(111) surface exposed to C_2H_4 **T = 975 K** P = 3 × 10⁻⁹ \rightarrow 1 × 10⁻⁸ mbar

G. Dong et al., ACS Nano **7**, 7028 (2013) New J. Phys. **14**, 053033 (2012) [*h*-BN on Rh(111): PRL **104**, 096102 (2010)]

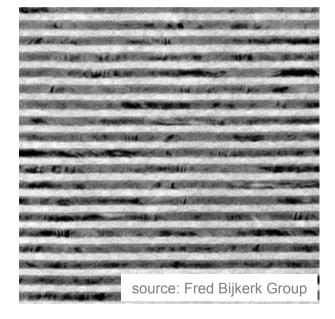






ARCNL prequel: EUV-optics

Mirror for λ = **13.5** nm Bilayer thickness: 6.25 nm (normal incidence)



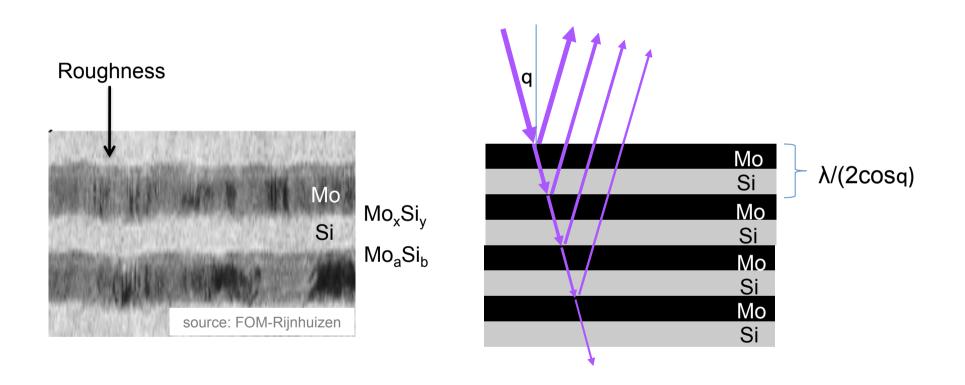
grown by E-beam evaporation or sputter deposition





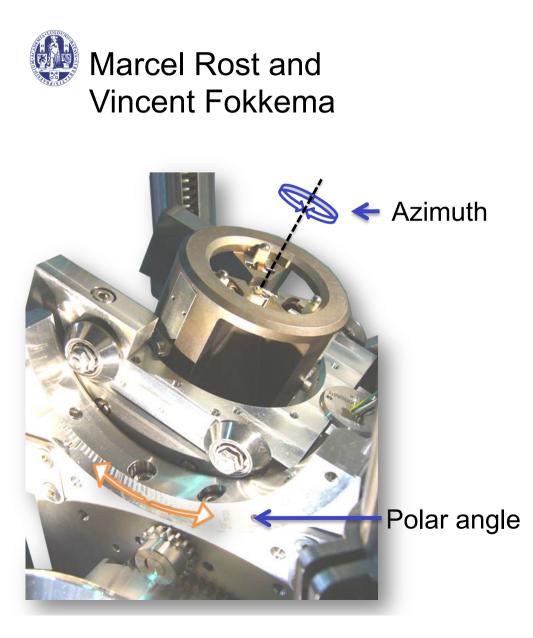


ARCNL prequel: EUV-optics



Why so rough!? Roughness reduces reflectivity

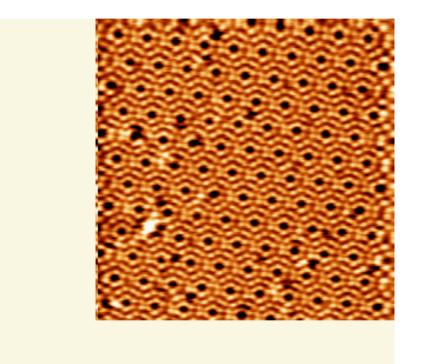
Depo-STM: in-situ growth / ion erosion





Live growth: Mo deposition on Si(111)

initial stages: silicide formation

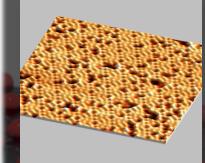


30 nm x 30 nm 1.7 s/frame 0-0.1 nm Mo



Marcel Rost Vincent Fokkema

Advanced Research Center for Nanolithography (ARCNL)



ASML

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CO₂ drive laser CO₂ drive laser Collector Lots of jobs: PhD students postdocs tenure trackers senior staff members technicians



